DESCRIPTION

The ES1AF~ES1JF is available in SMAF package

FEATURES

- For surface mounted applications
- Low profile package
- Glass Passivated Chip Junction
- Superfast reverse recovery time
- Available in SMAF package

ORDERING INFORMATION

Package Type	Part Number				
	ES1AF				
SMAF	ES1BF				
	ES1CF				
	ES1DF ES1EF				
					ES1GF
	ES1JF				
	Note	SPQ: 3,000pcs/Reel			
AiT provides all RoHS Compliant Products					

MECHANICAL DATA

Case: SMAF

Terminals: Solderable per MIL-STD-750,

Method 2026

Approx. Weight: 27mg 0.00086oz

PIN DESCRIPTION



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ABSOLUTE MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

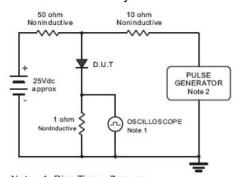
Ratings at 25°C ambient temperature unless otherwise specified. Single phase, half wave, 60 Hz, resistive or inductive load. For capacitive load, derate current by 20%

Parameter		Symbol	ES1AF	ES1BF	ES1CF	ES1DF	ES1EF	ES1GF	ES1JF	Unit
Maximum Repetitive Peak		V _{RRM}	50	100	150	200	300	400	600	V
Reverse Voltage	Reverse Voltage		50	100	150	200	300	400	600	V
Maximum RMS Volta	ge	V _{RMS}	35	70	105	140	210	280	420	V
Maximum DC Blockin	Maximum DC Blocking Voltage		50	100	150	200	300	400	600	٧
Maximum Average Fo	Maximum Average Forward		1.0							•
Rectified Current at T _L =100°C		I _{F(AV)}								Α
Peak Forward Surge	Peak Forward Surge Current									
8.3ms Single Half Sine Wave		Ігѕм								
Superimposed on Rated Load			25							A
(JEDEC Method)										
Maximum Forward Voltage at 1A		V _F	1.0 1.25 1.7					1.7	V	
Maximum DC										
Reverse Current at	T _A =25°C	I _R	5.0							
Rated DC	Rated DC T _A =125°C		100							uA
Blocking Voltage										
Typical Junction Cap	acitance at	e at		0						
V _R =4V, f=1MHz		Сл	10							pF
Maximum Reverse Recovery			35						20	
Time at I _F =0.5A, I _R =1A, I _{rr} =0.25A		t _{rr}							ns	
Operating and Storage		TJ,	-55 ~150							°C
Temperature Range		T _{STG}							C	

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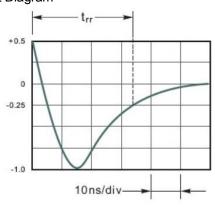
TYPICAL CHARACTERISTICS

Figure. 1 Reverse Recovery Time Characteristic And Test Circuit Diagram



Note: 1. Rise Time = 7ns, max. Input Impedance = 1megohm,22pF.

Ries Time =10ns, max.
Source Impedance = 50 ohms.



Set time Base for 10 ns/div

Figure. 2 Maximum Average Forward Current Rating

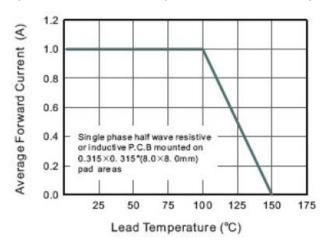


Figure. 4 Typical Forward Characteristics

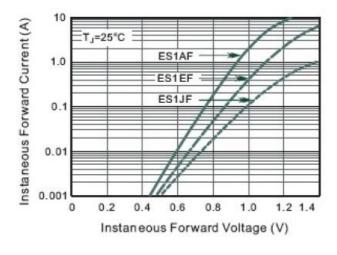


Figure. 3 Typical Reverse Characteristics

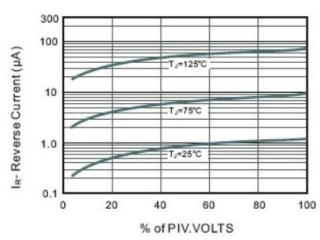
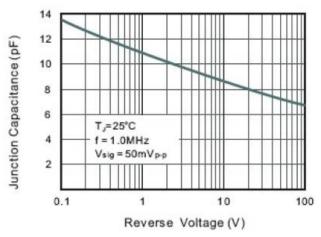


Figure. 5 Typical Junction Capacitance



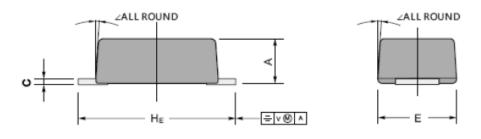
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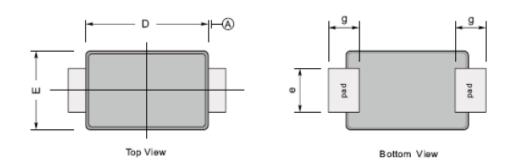
ES1AF~ES1JF

PACKAGE INFORMATION

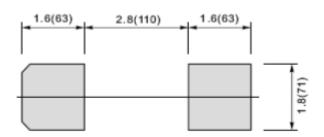
Dimension in SMAF (Unit: mm)

Plastic surface mounted package; 2 leads





The recommended mounting pad size



Unit: mm(mil)

UN	NIT	Α	В	С	Е	е	g	HE	∠
mm	Max	1.3	0.23	3.7	2.7	1.6	1.3	4.9	
	Min	1.1	0.18	3.3	2.4	1.3	1.0	4.4	7 °
mil	Max	51	9.1	146	106	63	51	193	7°
	Min	43	7.1	130	94	51	39	173	

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